

10/655,230 **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet	1	of	4	Filing Date	September 3, 2003
				First Named Inventor	Karim, M. Ziaul
				Art Unit	1762 2825
				Examiner Name	Unassigned 1. AWT/A
				Attorney Docket Number	A8313/T51200

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Examiner Initials ¹	Cite No. ¹	Document Number Number Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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		Application Number	10/655,230
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		First Named Inventor	Karim, M. Ziaul
		Art Unit	1762 2825
Examiner Name	Unassigned 1. ANYA		
Sheet 2	of 4	Attorney Docket Number	A8313/T51200

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				Art Unit	4762 2825
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Sheet	3	of	4	Attorney Docket Number	A8313/T51200

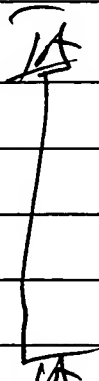

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				Art Unit	4762 2825
				Examiner Name	Unassigned J. ANYA
Sheet	4	of	4	Attorney Docket Number	A8313/T51200

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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	C22		

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INFORMATION PROCEDURE STATEMENT BY APPLICANT (use as many sheets as necessary)		10/655,230	
		Filing Date	03-03-2000
		First Named Inventor	Karim, M. Ziaul
		Art Unit	Unassigned 2825
		Examiner Name	Unassigned L. ANYA
Sheet 1	of 3	Attorney Docket Number	A8313/T51200

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				Filing Date	09-03-2003	
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				Art Unit	Unassigned 2825	
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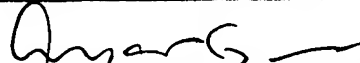
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